



NPN SURFACE MOUNT TRANSISTOR

Features

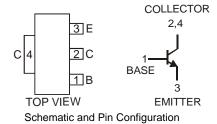
- **Epitaxial Planar Die Construction**
- Complementary PNP Type Available (DCX53)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Mechanical Data

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.072 grams (approximate)



SOT89-3L



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V _{CEO}	80	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	Ic	1	A
Peak Pulse Current	I _{CM}	1.5	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T _A = 25°C	P _D	1	W
Operating and Storage Temperature Range	T_j , T_{STG}	-55 to +150	°C
Thermal Resistance, Junction to Ambient Air (Note 3) @T _A = 25°C	$R_{ heta JA}$	125	°C/W

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 4)							
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$	100			V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	80	_		V	$I_C = 10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Volta	age	V _{(BR)EBO}	5.0	_		V	$I_E = 10\mu A, I_C = 0$
Collector-Base Cutoff Current		I _{CBO}	l		0.1 20	μА	$V_{CB} = 30V, I_E = 0$ $V_{CB} = 30V, I_E = 0, T_A = 150$ °C
Emitter-Base Cutoff Current		I _{EBO}		_	100	nA	$V_{EB} = 5.0V, I_C = 0$
ON CHARACTERISTICS (Note 4)							
DC Current Gain	DCX56, DCX56-16	h _{FE} -	63		_		$I_C = 5.0 \text{mA}, V_{CE} = 2.0 \text{V}$
	DCX36, DCX36-16		40				$I_C = 500 \text{mA}, V_{CE} = 2.0 \text{V}$
	DCX56		63	_	250		$I_C = 150 \text{mA}, V_{CE} = 2.0 \text{V}$
	DCX56-16		100	_	250	_	$I_C = 150 \text{mA}, V_{CE} = 2.0 \text{V}$
Collector-Emitter Saturation Voltage		V _{CE(SAT)}	_	_	0.5	V	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Base-Emitter Turn-On Voltage		V _{BE(ON)}	_	_	1.0	V	I _C = 500mA, V _{CE} = 2.0V
SMALL SIGNAL CHARACTERISTICS							
Current Gain-Bandwidth Product		f _T		200		MHz	$I_C = 50 \text{mA}, V_{CE} = 5 \text{V},$ f = 100MHz
Output Capacitance		C_{obo}		_	15	pF	$V_{CB} = 10V, I_E = 0, f = 1MHz$

No purposefully added lead. Notes:

- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- Measured under pulsed conditions. Pulse width = 300μ s. Duty cycle \leq 2%.



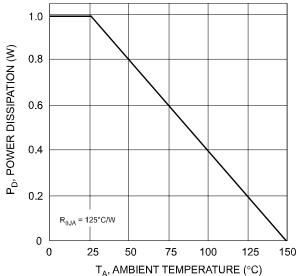
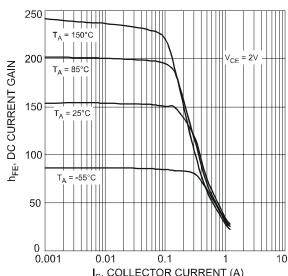
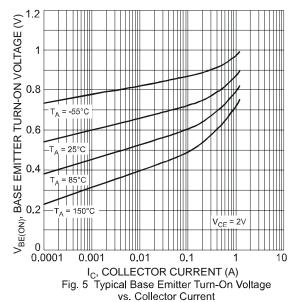


Fig. 1 Power Dissipation vs. Ambient Temperature



 $\rm I_{\rm C},$ COLLECTOR CURRENT (A) Fig. 3 Typical DC Current Gain vs. Collector Current



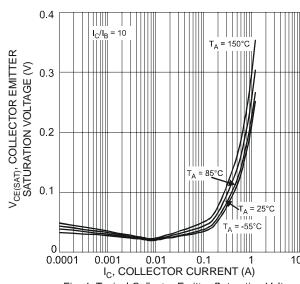


Fig. 4 Typical Collector Emitter Saturation Voltage vs. Collector Current

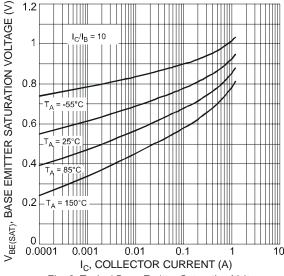
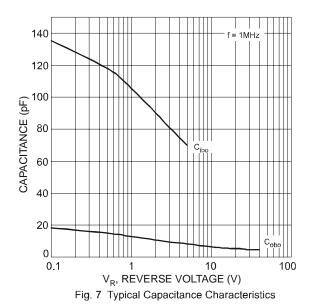
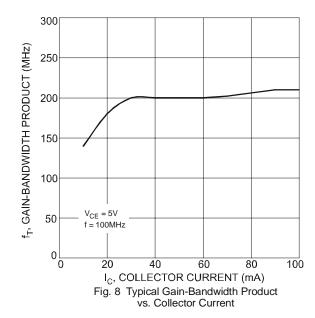


Fig. 6 Typical Base Emitter Saturation Voltage vs. Collector Current





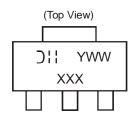


Ordering Information (Note 5)

Device	Packaging	Shipping
DCX56-13	SOT89-3L	2500/Tape & Reel
DCX56-16-13	SOT89-3L	2500/Tape & Reel

5. For packaging details, go to our website at http://www.diodes.com/ap02007.pdf. Notes:

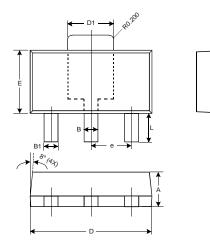
Marking Information

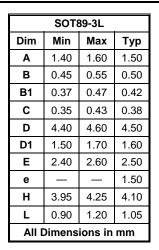


XXX = Product Type Marking Code ex. N18 = DCX56 N18-16 = DCX56-16

III = Manufacturer's code marking YWW = Date Code Marking Y = Last digit of year ex: 7 = 2007 WW = Week code 01 - 52

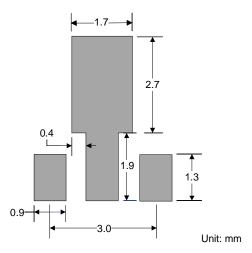
Package Outline Dimensions







Suggested Pad Layout



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